

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/667,277	09/19/2003	C. Christopher Klepper	8651	
7590 06/07/2006			EXAMINER	
James W. Hiney			PERKINS, PAMELA E	
Suite 1000 1872 Pratt Drive			ART UNIT	PAPER NUMBER
Blacksburg, VA 24060			2822	
		DATE MAILED: 06/07/2006		

Please find below and/or attached an Office communication concerning this application or proceeding.

1) Notice of References Cited (PTO-892)

Paper No(s)/Mail Date 5/5/06.

2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)

4) Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.

6) Other:

5) Notice of Informal Patent Application (PTO-152)

Application/Control Number: 10/667,277

Art Unit: 2822

DETAILED ACTION

This office action is in response to the filing of the after final amendment on 5 May 2006. Claims 1-30, 32-36, 38 and 40-45 are pending; claims 31, 37, 39 and 46-48 have been cancelled.

Applicant's request for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 4, 5, 9, 28 and 33 are rejected under 35 U.S.C. 102(b) as being anticipated by Leung (5,558,718) ("Leung '718").

Referring to claim 4, Leung '718 discloses a method of ion implantation doping in a vacuum wherein plasma is involved in virtually 100% ionized pure boron plasma, meaning no other ionized atom species and no other non-ionized gas atoms in the plasma source (col. 3, lines 6-18; col. 4, lines 51-58; col. 4, line 66 thru col. 5, line 9).

Referring to claim 5, Leung '718 further discloses wherein the boron ions and ions of other atomic species have organized in a boron compound electrode (col. 5, lines 22-28).

Application/Control Number: 10/667,277

Art Unit: 2822

Referring to claim 9, Leung '718 also discloses the total ion arrival rate or ion implantation rate, expressed as a total electric current impinging on the target material, is 1 amp (col. 9, lines 16-25).

Referring to claim 28, Leung '718 discloses wherein every process including steps of providing for generation of plasma and streaming of boron ions to the target are conducted with all components in a vacuum (col. 9, line 47 thru col. 10, line 11).

Referring to claim 33, Leung '718 further discloses implanting boron at doses normally used for p-doping due to the extraordinary damage rate associated with the high temperature rate (col. 1, lines 39-45; col. 4, line 66 thru col. 5, line 9).

Claims 33 and 34 are rejected under 35 U.S.C. 102(b) as being anticipated by Leung (5,517,084) ("Leung '084").

Referring to claim 33, Leung '084 discloses a method of ion implantation of boron into semiconductor silicon in which the target is amorphized at boron doses normally used for p-doping due to the extraordinary damage rate associated with the high temperature rate, wherein the method takes place in a vacuum (col. 3, lines 43-57).

Referring to claim 34, Leung 0'84 further discloses wherein the target may be deliberately heated to a desired temperature by the implantation process due to the extraordinary rate of heat deposition resulting from the high rate of ion deposition (col. 3, lines 49-57; col. 7, lines 48-57).

Allowable Subject Matter

Claim 29 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: referring to claim 29, prior art does not teach, suggest or disclose wherein the vacuum precludes deliberate introduction any non-solid matter other than the plasma and ions originating in the solid electrode.

Claims 1-3, 6-8, 10-27, 30, 32, 35, 36, 38, and 40-45 are allowed.

The following is an examiner's statement of reasons for allowance: referring to claim 1, prior art does not anticipate, teach, or suggest a method of implanting boron ions into semiconductor materials at specified energies in the absence of a gas or vapor, where the ions or plasma originate directly from a solid boron material.

Response to Arguments

Applicant's arguments, see the after final amendment filed 5 May 32006, with respect to the rejection(s) of claim(s) 4, 5, 9, 28, 33 and 34 under 35 U.S.C. 102 (b) have been fully considered and are persuasive. Therefore, the rejection has been withdrawn. However, upon further consideration, a new ground(s) of rejection is made in view of Leung '718 and Lueng '084.

Application/Control Number: 10/667,277

Art Unit: 2822

Conclusion

Page 5

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Pamela E. Perkins whose telephone number is (571) 272-1840. The examiner can normally be reached on Monday thru Friday, 8:30am to 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Zandra Smith can be reached on (571) 272-2429. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call-800-786-9199 (IN USA OR CANADA) or 571-272-1000.

PEP

30 May 2006

Zandra V. Smith

Supervisory Patent Examiner

30 May 2004